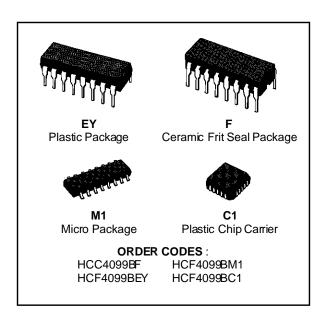


HCC/HCF4099B

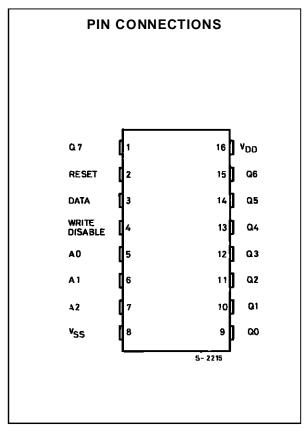
8-BIT ADDRESSABLE LATCH

- SERIAL DATA INPUT ACTIVE PARALLEL OUTPUT
- STORAGE REGISTER CAPABILITY MASTER CLEAR
- CAN FUNCTION AS DEMULTIPLEXER
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



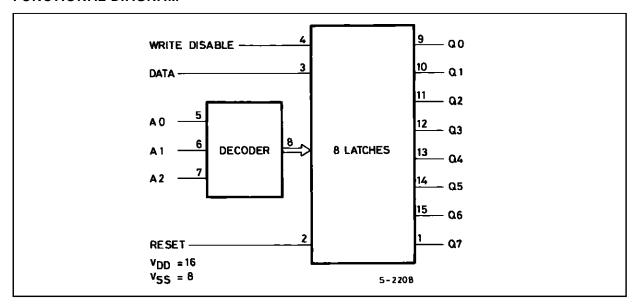
DESCRIPTION

The **HCC4099B** (extended temperature range) and HCF4099B (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The HCC/HCF4099B 8-bit addressable latch is a serial-input, parallel-output storage register that can perform a variety of functions. Data are inputted to a particular bit in the latch when that bit is addressed (by means of inputs A0, A1, A2) and when WRITE DISABLE is at a low level. When WRITE DISABLE is high, data entry is inhibited; however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs. A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer; the bit that is addressed has an active output which follows the data input, while all unaddressed bits are held to a logic "0" level.



September 1988 1/14

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
Vi	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I_1	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
Тор	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

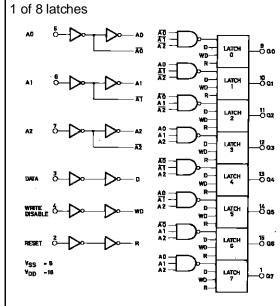
* All voltage values are referred to V_{SS} pin voltage.

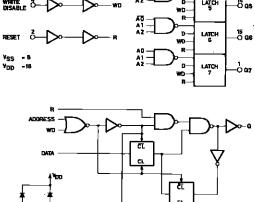
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	> >
Vı	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C ℃



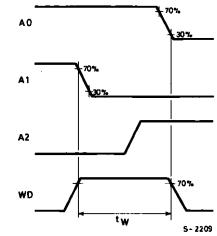
LOGIC DIAGRAM





ALL INPUTS ARE PROTECTED BY COS! MOS PROTECTION NETWORK

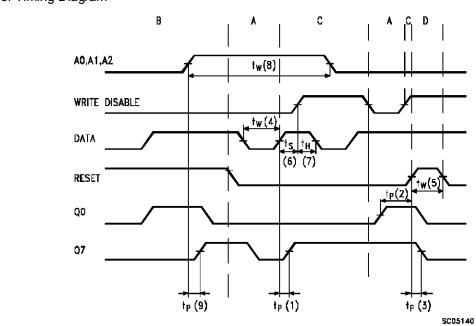
Definition of WRITE DIABLE ON Time



	Mode Selection							
Types	WD R		Addressed Latch	Unaddressed Latch				
А	0	0	Follows Data	Holds Previous State				
В	0	1	Follows Data (active high demulti					
С	1	0	Holds Previous State					
D	1	1	Reset to "0"	Reset to "0"				

WD = WRITE DISABLE R = RESET

Master Timing Diagram



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	s	Value							
Symbol	Parameter		V _I (V)	۷o	I ₀	V _{DD}	ΤL	o w*		25°C		T _{Hi}	gh*	Unit
				(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
IL	Quiescent		0/ 5			5		5		0.04	5		150	
	Current	нсс	0/10			10		10		0.04	10		300	
		Types	0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	μΑ
			0/ 5			5		20		0.04	20		150	
		HCF Types	0/10			10		40		0.04	40		300	
		Types	0/15			15		80		0.04	80		600	
Voh	Output Hig	h	0/ 5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
VoL	Output Low	ı	5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
Гон	Output		0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		
	Drive	HCC	0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
	Current	Types	0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		mA
			0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		IIIA
		HCF	0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
I _{OL}	Output		0/ 5	0.4		5	0.64		0.51	1		0.36		
	Sink	HCC Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	Types	0/15	1.5		15	4.2		3.4	6.8		2.4		mΛ
		0/ 5	0.4		5	0.52		0.44	1		0.36		mA	
		HCF Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		Types	0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage	HCC Types	0/18	Any In	put	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μА
	Current	HCF Types	0/15	, ary iii		15		± 0.3		±10 ⁻⁵	± 0.3		± 1	μ, τ
C_1	Input Capa	citance		Any In	put					5	7.5			pF

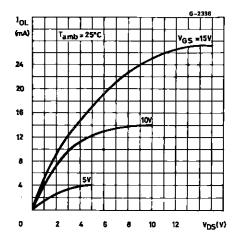
^{*} $T_{LOW} = -55^{\circ}C$ for HCC device : $-40^{\circ}C$ for HCF device. * $T_{HIGH} = +125^{\circ}C$ for HCC device : $+85^{\circ}C$ for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$,



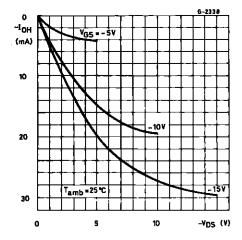
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, $R_{L} = 200 k\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}C$, all input rise and fall times = 20ns)

			Test Conditions			Value		
Symbol	Par	ameter	(see master timing diagram)	V _{DD} (V)	Min.	Тур.	Max.	Unit
t _{PLH} , t _{PHL} Propagation		Data to Output		5		200	400	
	Delay Time		(1)	10		75	150	
				15		50	100	
		Write Disable to		5		200	400	
		Output	(2)	10		80	160	
				15		60	120	ns
		Address to		5		225	450	113
		Output	(9)	10		100	200	
				15		75	150	
t _{PHL}	Propagation	Reset to Output		5		175	350	
	Delay Time		(3)	10		80	160	
				15		65	130	
t_{THL}, t_{TLH}	Transition	Any Output		5		100	200	
	Time			10		50	100	ns
				15		40	80	
tw	Pulse Width	Data		5	200	100		
			(4)	10	100	50		
				15	80	40		
		Address		5	400	200		
			(8)	10	200	100		ns
				15	125	65		
		Reset		5	150	75		
			(5)	10	75	40		
				15	50	25		
t _{setup}	t _{setup} Setup Time Data to Writ Disable	Data to Write		5	100	50		
		Disable	(6)		50	25		ns
				15	35	20		
t _{hold}	Hold Time	Data to Write		5	150	75		
		Disable	(7)	10	75	40		ns
		<u> </u>		15	50	25		

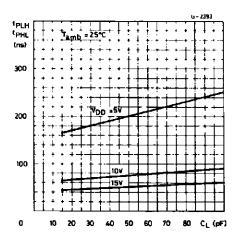
Typical Output Low (sink) Current Characteristics.



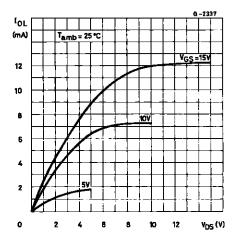
Typical Output High (source) Current Characteristics.



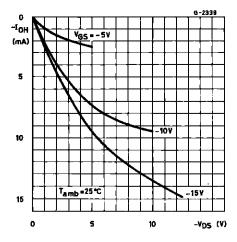
Typical Propagation Delay Time (data to Qn) vs. Load Capacitance.



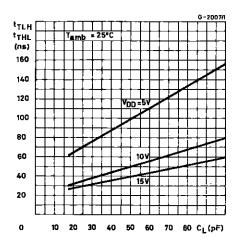
Minimum Output Low (sink) Current Characteristics.



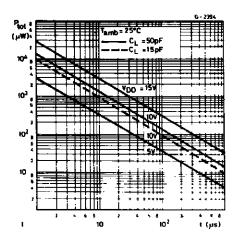
Minimum Output High (source) Current Characteristics.



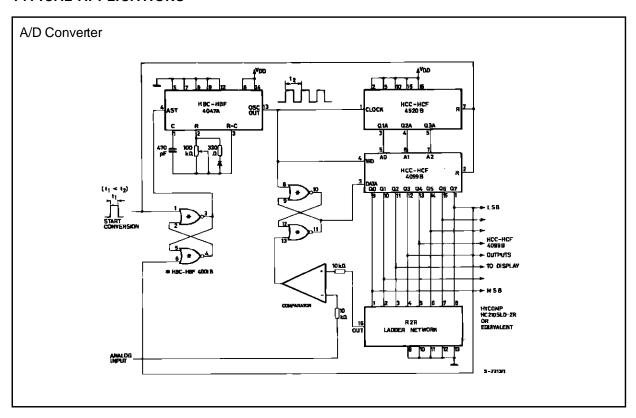
Typical Transition Time vs. Load Capacitance.



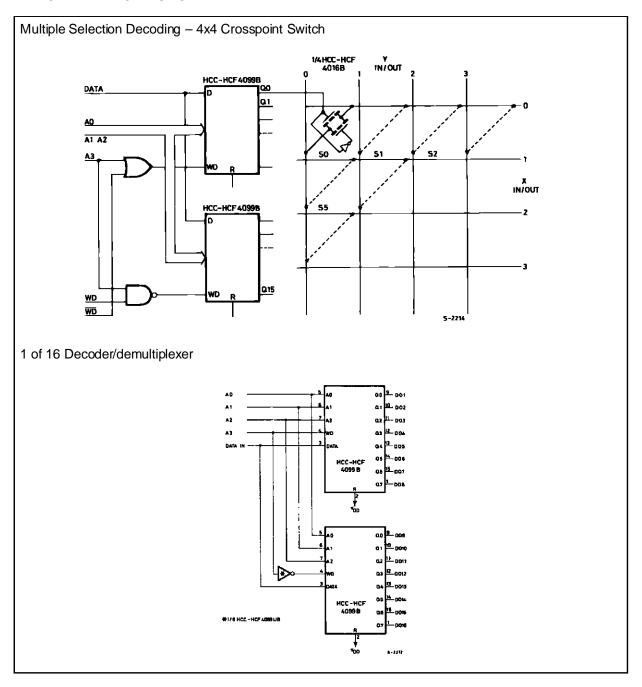
Typical Dynamic power Dissipation vs. Address Cycle Time.



TYPICAL APPLICATIONS

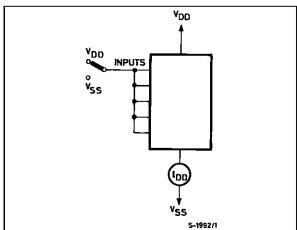


TYPICAL APPLICATIONS

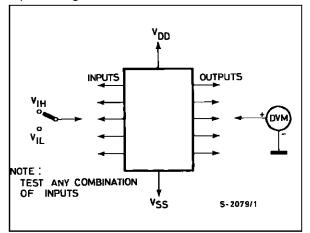


TEST CIRCUITS

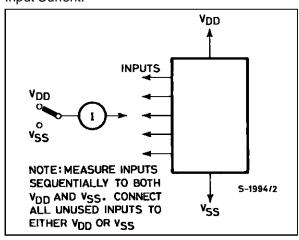
Quiescent Device Current.



Input Voltage.

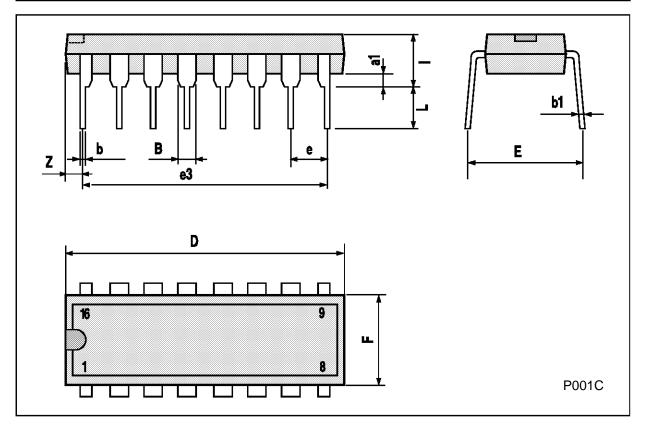


Input Current.



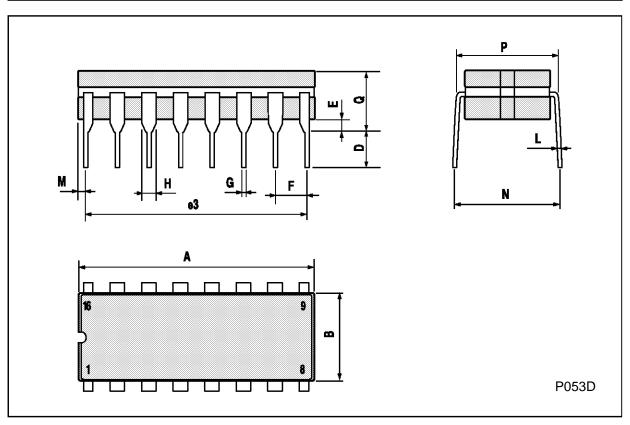
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



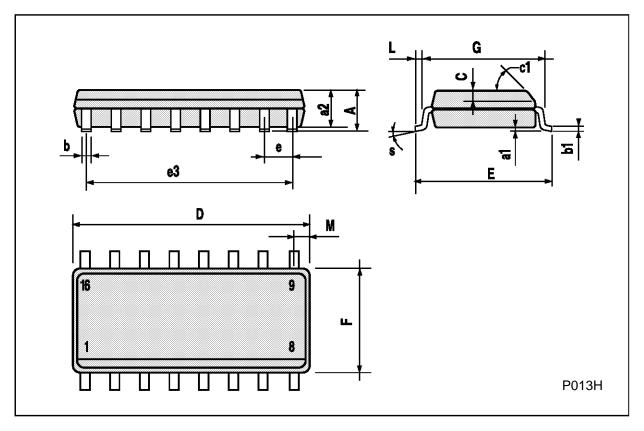
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch				
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			20			0.787		
В			7			0.276		
D		3.3			0.130			
Е	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	0.51		1.27	0.020		0.050		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



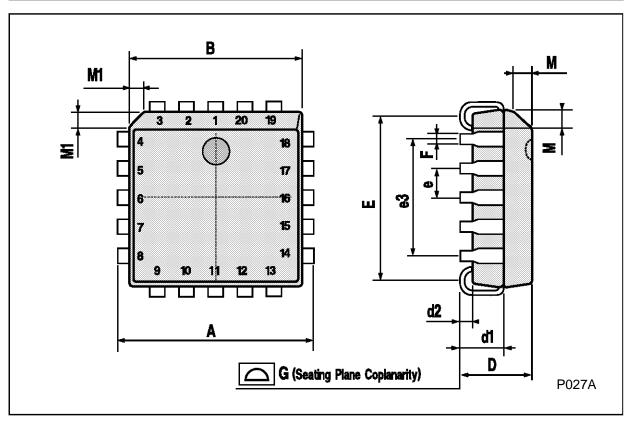
SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch			
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.068	
a1	0.1		0.2	0.004		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)			
D	9.8		10	0.385		0.393	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		8.89			0.350		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.62			0.024	
S			8° (max.)			



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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